■ NMOS Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250μA	60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V, V_{GS}=0V	-	-	1	μA
		V_{DS}=60V, V_{GS}=0V, Tj=150	-	-	100	
Gate-Body Leakage Current	I_{GSS}	V_{GS}= ± 20V, V_{DS}=0V	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=250μA	1	1.5	2.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=20A	-	23	30	mΩ
		V_{GS}				

■ NMOS Typical Electrical and Thermal Characteristics Diagrams

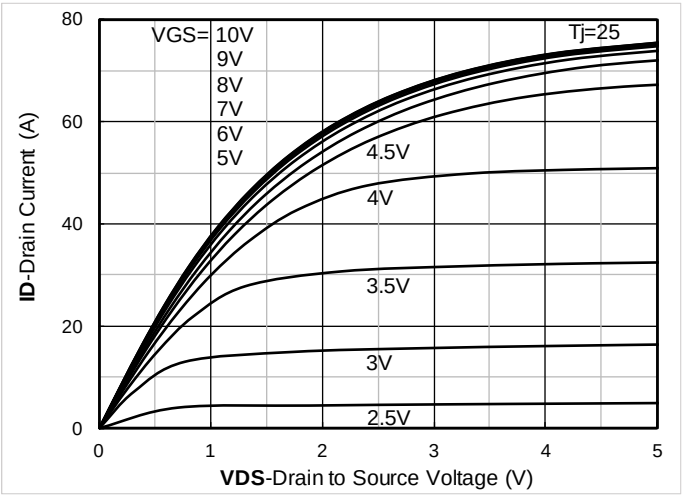

Figure 1. Output Characteristics

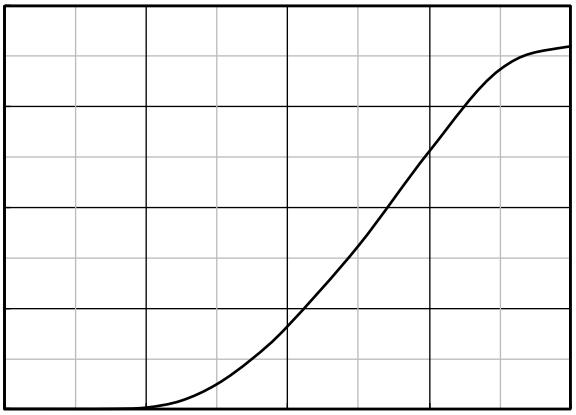

Figure 2. Transfer Characteristics

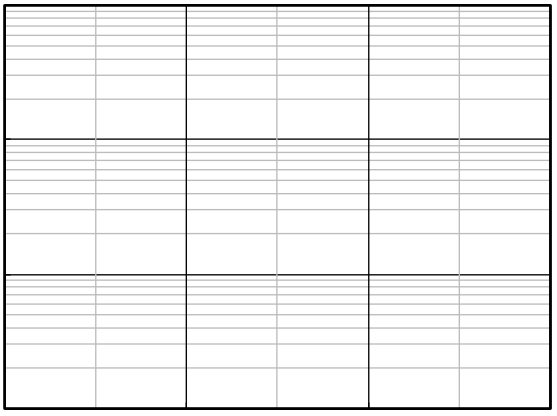

Figure 3. Capacitance Characteristics

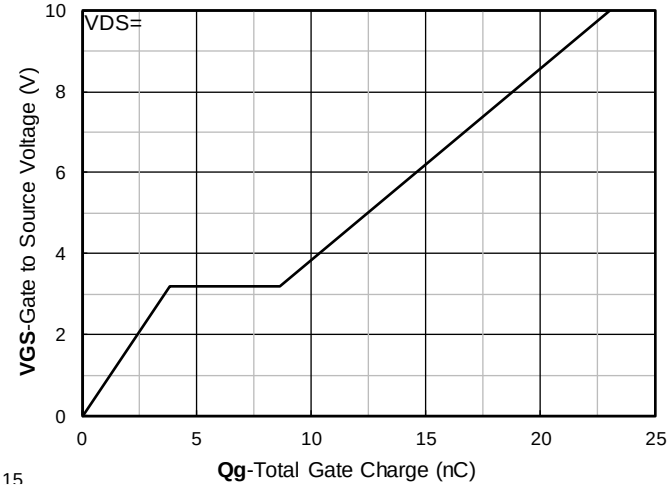

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Figure 4. Gate Charge

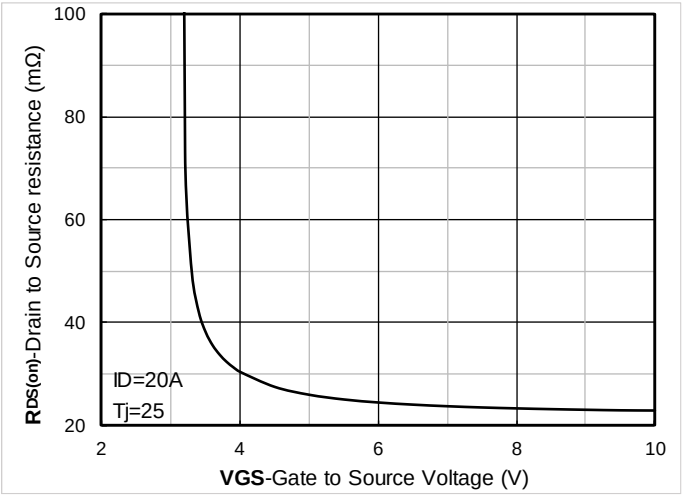


Figure 5. On-Resistance vs Gate to Source Voltage

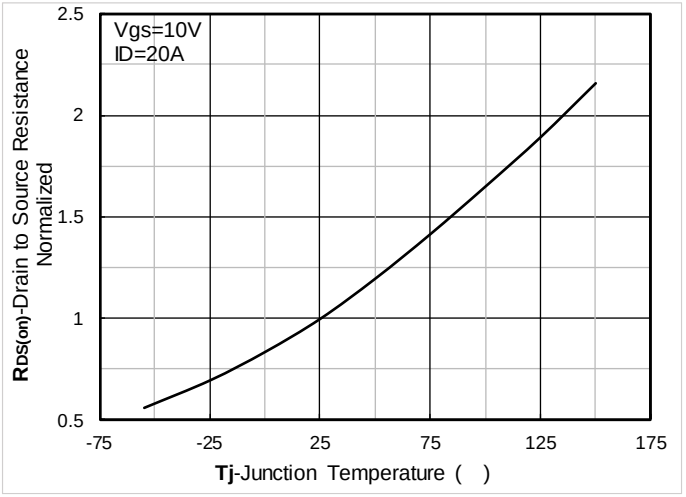


Figure 6. Normalized On-Resistan

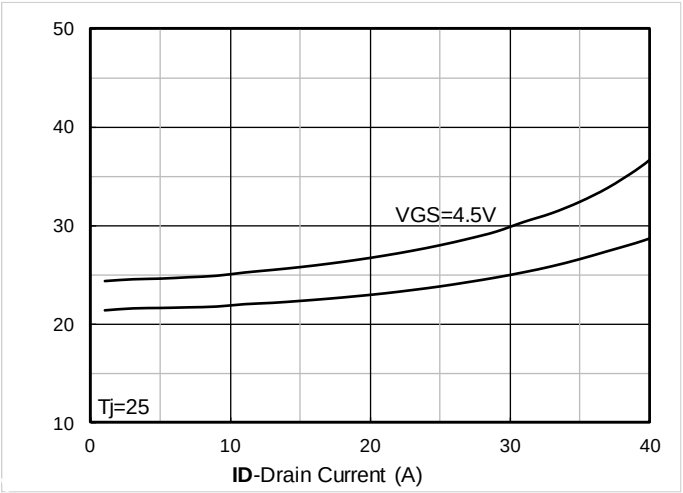


Figure 7. $R_{DS(on)}$ VS Drain Current

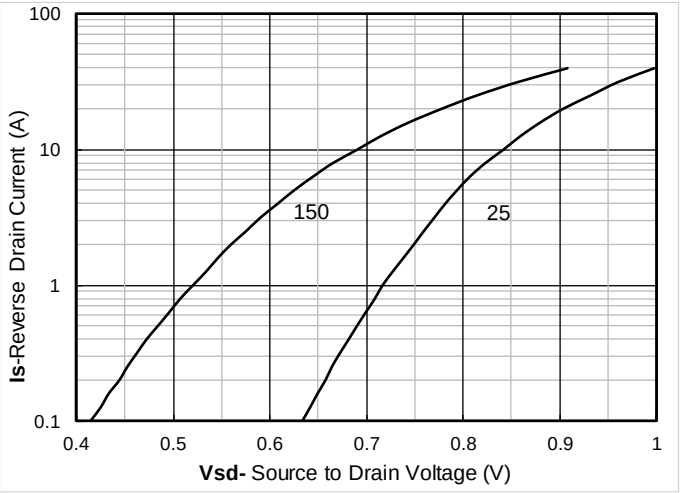
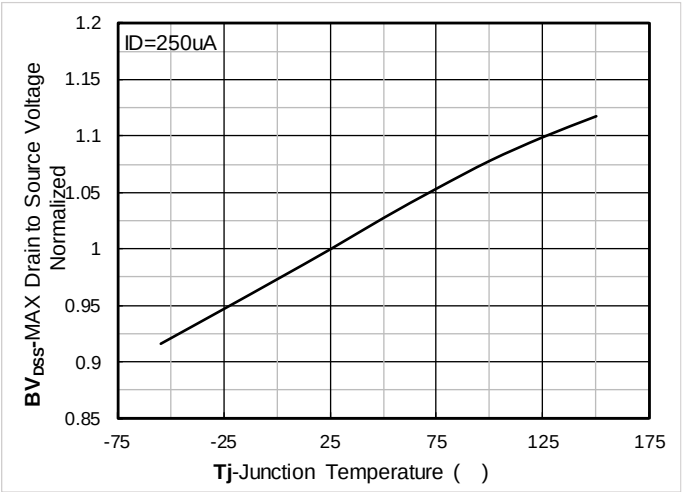


Figure 8. Forward characteristics of reverse diode



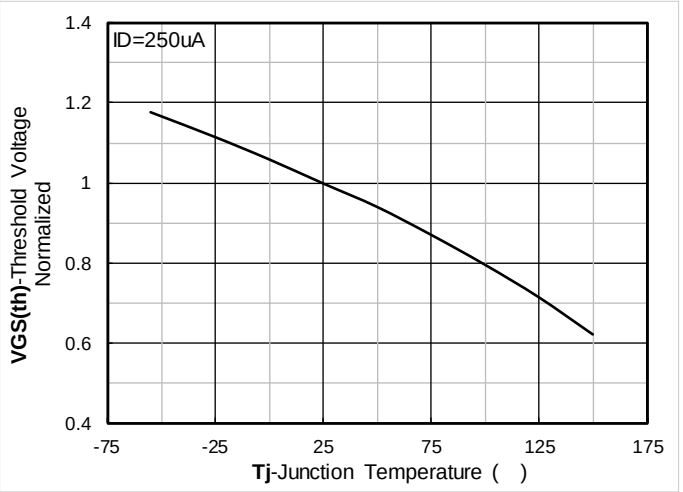
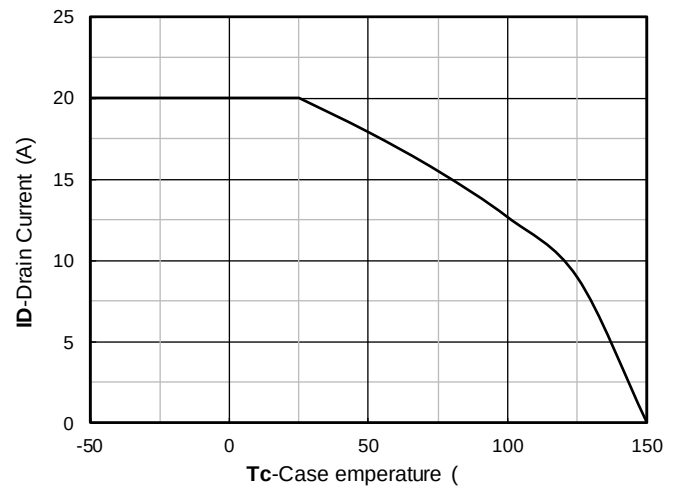


Figure 9. Normalized breakdown voltage Figure 10. Normalized Gate Threshold Voltage



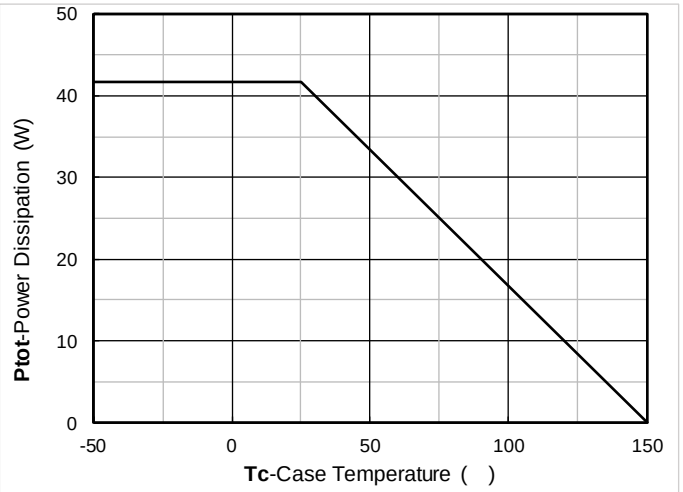
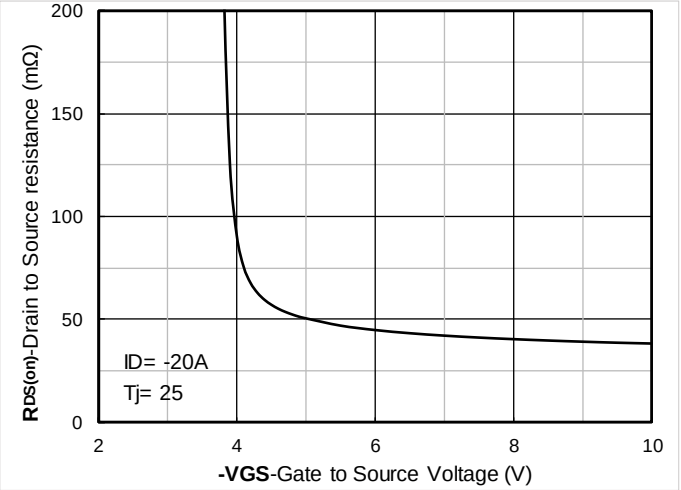


Figure 11. Current dissipation



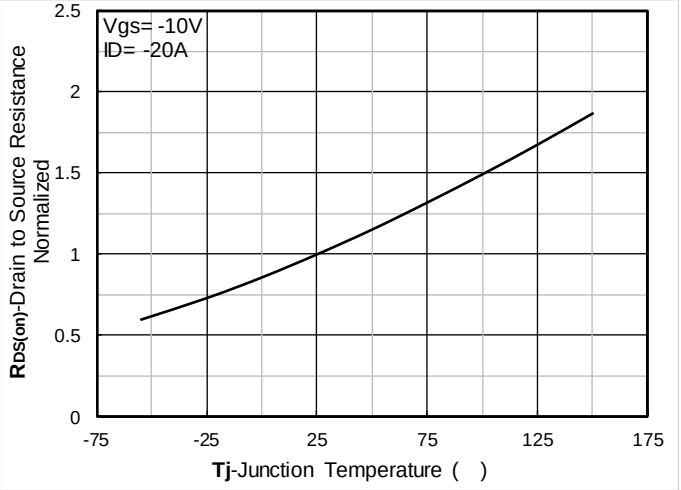


Figure 5. On-Resistance vs Gate to Source Voltage

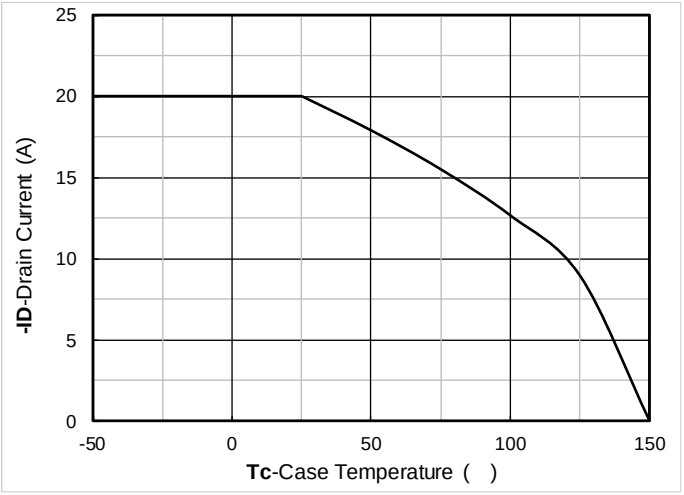


Figure 11. Current dissipation

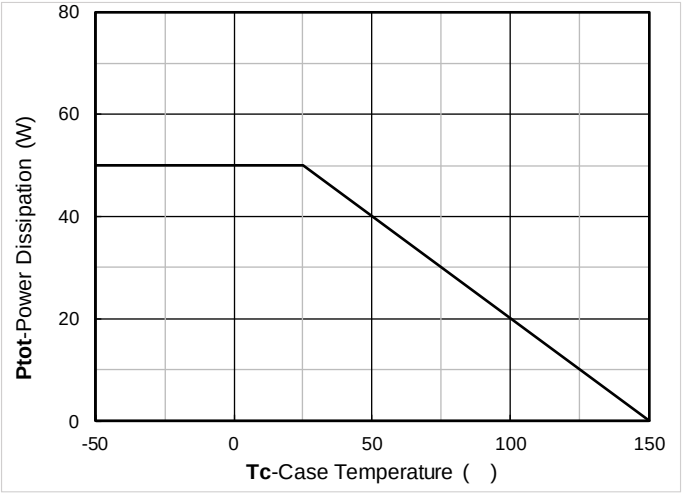


Figure 12. Power dissipation

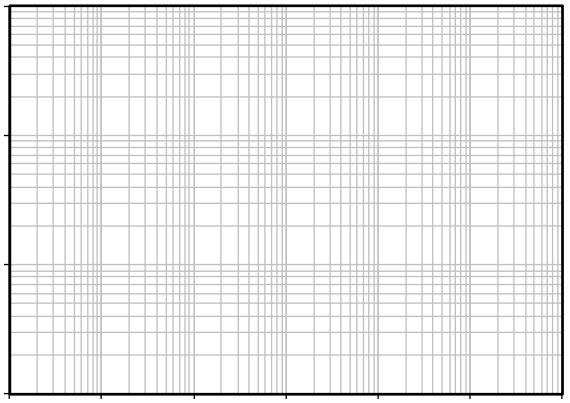


Figure 13. Maximum Transient Thermal Impedance

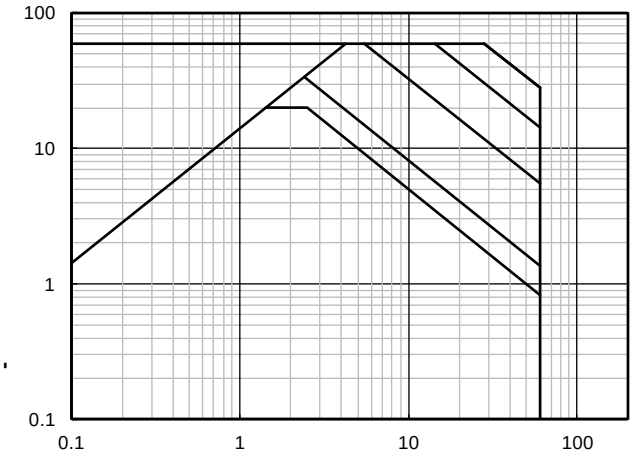


Figure 14. Safe Operation Area

■ **PDFN5060-8L-E-1.1MM**

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